ON Semiconductor®

Energy Efficient Innovations

Product Overview

NSS12601CF8: Low $V_{CE(sat)}$ Transistor, NPN, 12 V, 8.0 A

For complete documentation, see the data sheet

Product Description

Low $V_{CE(sat)}$ Bipolar Transistors are miniature surface mount devices featuring ultra low saturation voltage $V_{CE(sat)}$ and high current gain capability. These are designed for use in low voltage, high speed switching applications where affordable efficient energy control is important.

Features

- High Current, Low $V_{CE(sat)}$, ESD Robust, High Current Gain, High Cut Off Frequency, Low Profile Package, Linear Gain (Beta)

Benefits

- Improved Circuit Efficiency, Decreased Battery Charge Time, Reduce component count, High Frequency Switching, Smaller Portable Product, No distortion

Applications

- Load Switching, Battery Charging, External Pass Transistor, DC/DC Converter, Complimentary Driver, Current Extention & Low Drop Out Regulation, Cathode Florescent Lamp drive, Peripheral Driver - LEDs, Motors, Relays

Part Electrical Specifications

Product	Compliance	Status	Polarity	I_C Continuous (A)	$V_{(BR)CEO}$ Min (V)	$V_{CE(sat)}$ Max (V)	h_{FE} Min	h_{FE} Max	f_T Min (MHz)	P_{TM} Max (W)	Package Type
NSS12601CF8T1G	AEC Qualified Pb-free Halide free	Active	NPN	6	12	0.05	200	-	140	1.4	ChipFET-8

For more information please contact your local sales support at www.onsemi.com

Created on: 7/11/2015